Four-Channel, 5kV_{RMS} Digital Isolators

General Description

The MAX14934–MAX14936 are a family of four-channel, $5kV_{RMS}$ digital isolators utilizing Maxim's proprietary process technology. For applications requiring $2.75kV_{RMS}$ of isolation, see the MAX14930–MAX14932. The MAX14934–MAX14936 family transfers digital signals between circuits with different power domains at ambient temperatures up to $+125^{\circ}C$.

The MAX14934–MAX14936 family offers all three possible unidirectional channel configurations to accommodate any four-channel design, including SPI, RS-232, RS-485, and large digital IO modules. For applications requiring bidirectional channels, such as I²C, refer to the MAX14937.

Devices are available with data rates from DC up to 1Mbps, 25Mbps, or 150Mbps. Each device is also available in either a default high or default low configuration. The default is the state an output goes to when its input is unpowered. See the *Product Selector Guide* and *Ordering Information* for the suffixes associated with each option.

Independent 1.71V to 5.5V supplies on each side of the isolator also make the devices suitable for use as level translators.

The MAX14934–MAX14936 are available in a 16-pin wide body (10.3mm x 7.5mm) SOIC package. All devices are rated for operation at ambient temperatures of -40°C to +125°C.

<u>Product Selector Guide</u> and <u>Ordering Information</u> appear at end of data sheet.

Benefits and Features

- Robust Galvanic Isolation of Digital Signals
 - Withstands 5kV_{RMS} for 60s (V_{ISO})
 - Continuously Withstands 848V_{RMS} (V_{IOWM})
 - 1200V_P Repetitive Peak Voltage (V_{IORM})
 - Withstands ±10kV Surge per IEC 61000-4-5
- Interfaces Directly with Most Micros and FPGAs
 - · Accepts 1.71V to 5.5V Supplies
- Many Options Support Broad Applications
 - 3 Data Rates (1Mbps, 25Mbps, 150Mbps)
 - 3 Channel Direction Configuration
 - 2 Output Default States (High or Low)
- Low Power Consumption at High Data Rates At 1.8V:
 - 2.5mA per Channel Typical at 1Mbps
 - 5.25mA per Channel Typical at 100Mbps At 3.3V²
 - 2.6mA per Channel Typical at 1Mbps
 - 7.1mA per Channel Typical at 100Mbps

Safety Regulatory Approvals

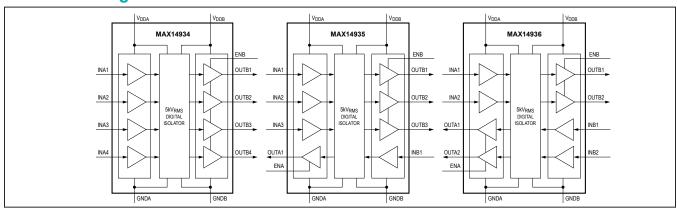
(see Safety Regulatory Approvals)

- UL According to UL1577
- cUL According to CSA Bulletin 5A
- VDE 0884-11 Basic Insulation

Applications

- Fieldbus Communications for Industrial Automation
- Isolated SPI, RS-232, RS-485/RS-422
- General Multichannel Isolation Applications
- Battery Management
- Medical Systems

Functional Diagram





Absolute Maximum Ratings

V _{DDA} to GNDA, V _{DDB} to GNDB	0.3V to +6V	Continuous Power Dissipation (T _A = +70°C)
INA_, ENA to GNDA	0.3V to +6V	Wide SOIC (derate 14.1mW/°C above +70°C) 1126.8mW
INB_, ENB to GNDB	0.3V to +6V	Operating Temperature Range40°C to +125°C
OUTA_ to GNDA0.	.3V to (V _{DDA} + 0.3V)	Maximum Junction Temperature+150°C
OUTB_ to GNDB0.	.3V to (V _{DDB} + 0.3V)	Storage Temperature Range65°C to +150°C
Short-Circuit Duration		Lead Temperature (soldering, 10s)+300°C
(OUTA_ to GNDA, OUTB_ to GNDB)	Continuous	Soldering Temperature (reflow)+260°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Package Information

PACKAGE TYPE: 16 Wide SOIC	
Package Code	W16M+8
Outline Number	21-0042
Land Pattern Number	90-0107
THERMAL RESISTANCE, FOUR-LAYER BOARD	
Junction to Ambient (θ _{JA})	71°C/W
Junction to Case (θ_{JC})	23°C/W

Package thermal resistances were obtained using the method described in JEDEC specification JESD51-7, using a four-layer board. For detailed information on package thermal considerations, refer to www.maximintegrated.com/thermal-tutorial.

For the latest package outline information and land patterns (footprints), go to www.maximintegrated.com/packages. Note that a "+", "#", or "-" in the package code indicates RoHS status only. Package drawings may show a different suffix character, but the drawing pertains to the package regardless of RoHS status.

DC Electrical Characteristics

 $(V_{DDA} - V_{GNDA} = +1.71V \text{ to } +5.5V, \ V_{DDB} - V_{GNDB} = +1.71V \text{ to } +5.5V, \ C_L = 15pF, \ T_A = -40^{\circ}C \text{ to } +125^{\circ}C, \ unless \text{ otherwise noted.}$ Typical values are at $V_{DDA} - V_{GNDA} = +3.3V, \ V_{DDB} - V_{GNDB} = +3.3V, \ V_{GNDA} = V_{GNDB}, \ T_A = +25^{\circ}C, \ unless \text{ otherwise noted.}$ (Note 1)

PARAMETER	SYMBOL	СО	CONDITIONS		TYP	MAX	UNITS
POWER SUPPLY							
Onerating Cumply Valtage	V _{DDA}	Relative to GNDA		1.71		5.5	V
Operating Supply Voltage	V_{DDB}	Relative to GNDB		1.71		5.5	V
Undervoltage Lockout Threshold	V _{UVLO} _	V _{DD} rising		1.45	1.58	1.71	V
Undervoltage Lockout Threshold Hysteresis	V _{UVLO} _ HYST				50		mV
			V _{DDA} = 5V		1.2	1.9	
		500kHz	V _{DDA} = 3.3V		1.2	1.9	
		square wave	V _{DDA} = 2.5V		1.2	1.9	
			V _{DDA} = 1.8V		1.1	1.9	
	I _{DDA}	12.5MHz square wave (Note 2)	V _{DDA} = 5V		2.1	2.7	
			V _{DDA} = 3.3V		2	2.7	-
			V _{DDA} = 2.5V		2	2.7	
			V _{DDA} = 1.8V		2	2.6	
			V _{DDA} = 5V		5	6.6	
		50MHz square wave (Note 2)	$V_{DDA} = 3.3V$		4.6	6.1	
			V _{DDA} = 2.5V		4.5	6.0	
Supply Current (MAX14934)			V _{DDA} = 1.8V		4.5	6.0	
Supply Current (MAX14934_)			V _{DDB} = 5V		8.1	11.2	mA
		500kHz	V _{DDB} = 3.3V		7.9	11.1	
		square wave	V _{DDB} = 2.5V		7.9	11.0	
			V _{DDB} = 1.8V		7.7	10.8	1
			$V_{DDB} = 5V$		12.8	15.9	
		12.5MHz square wave	$V_{DDB} = 3.3V$		11.1	14.2	
	I _{DDB}	(Note 2)	V _{DDB} = 2.5V		10.2	13.4	
		, ,	V _{DDB} = 1.8V		9.4	12.4	
			V _{DDB} = 5V		27.2	35.4	
		50MHz square wave	V _{DDB} = 3.3V		21.7	27.8	
		(Note 2)	V _{DDB} = 2.5V		17.6	23.0	
		, ,	V _{DDB} = 1.8V		14.4	18.9	

DC Electrical Characteristics (continued)

 $(V_{DDA} - V_{GNDA} = +1.71 \text{V to } +5.5 \text{V}, V_{DDB} - V_{GNDB} = +1.71 \text{V to } +5.5 \text{V}, C_L = 15 \text{pF}, T_A = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}, \text{ unless otherwise noted.}$ $Typical \ values \ are \ at \ V_{DDA} - V_{GNDA} = +3.3 \text{V}, V_{DDB} - V_{GNDB} = +3.3 \text{V}, V_{GNDA} = V_{GNDB}, T_A = +25 ^{\circ}\text{C}, \text{ unless otherwise noted.}$ (Note 1)

PARAMETER	SYMBOL	СО	NDITIONS	MIN	TYP	MAX	UNITS
			V _{DDA} = 5V		3.4	5.3	
		500kHz	V _{DDA} = 3.3V		3.3	5.3	
		square wave	V _{DDA} = 2.5V		3.3	5.3	
			V _{DDA} = 1.8V		3.2	5.1]
			V _{DDA} = 5V		5.6	7.1	
		12.5MHz	V _{DDA} = 3.3V		5	6.6	
	I _{DDA}	square wave (Note 2)	V _{DDA} = 2.5V		4.7	6.4	
		(. 1010 _)	V _{DDA} = 1.8V		4.5	6.1	
			V _{DDA} = 5V		12.4	16.0]
			50MHz V _{DDA} = 3.3V 10.1	13.0			
		square wave (Note 2)	V _{DDA} = 2.5V		9.1	11.6	mA
Cumply Current (MAV1402E)		,	V _{DDA} = 1.8V		8.2	10.4	
Supply Current (MAX14935_)		500kHz square wave	V _{DDB} = 5V		6.5	9.2	
			V _{DDB} = 3.3V		6.4	9.1	
			V _{DDB} = 2.5V		6.3	9.1	
			V _{DDB} = 1.8V		6.2	8.9	
			V _{DDB} = 5V		10.3	12.8	
		12.5MHz	V _{DDB} = 3.3V		8.9	11.6	1
	I _{DDB}	square wave (Note 2)	V _{DDB} = 2.5V		8.2	11.0	
		(V _{DDB} = 1.8V		7.6	10.3	- - - -
			V _{DDB} = 5V		22.7	29.1	
		50MHz	V _{DDB} = 3.3V		17.7	23.0	
		square wave (Note 2)	V _{DDB} = 2.5V		14.7	19.4	
		(14016-2)	V _{DDB} = 1.8V		11.9	15.9	

DC Electrical Characteristics (continued)

 $(V_{DDA} - V_{GNDA} = +1.71 \text{V to } +5.5 \text{V}, V_{DDB} - V_{GNDB} = +1.71 \text{V to } +5.5 \text{V}, C_L = 15 \text{pF}, T_A = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}, \text{ unless otherwise noted.}$ $Typical \ values \ are \ at \ V_{DDA} - V_{GNDA} = +3.3 \text{V}, V_{DDB} - V_{GNDB} = +3.3 \text{V}, V_{GNDA} = V_{GNDB}, T_A = +25 ^{\circ}\text{C}, \text{ unless otherwise noted.}$ (Note 1)

PARAMETER	SYMBOL	COI	NDITIONS	MIN	TYP	MAX	UNITS
			V _{DDA} = 5V		5.2	7.2	
		500kHz	V _{DDA} = 3.3V		5.2	7.2	
		square wave	V _{DDA} = 2.5V		5.2	7.2	
			V _{DDA} = 1.8V		5	7.0	
			V _{DDA} = 5V		8.2	10.0	
		12.5MHz	V _{DDA} = 3.3V		7.2	9.1	
	I _{DDA}	square wave (Note 2)	V _{DDA} = 2.5V		6.7	8.7	
			V _{DDA} = 1.8V		6.3	8.2	
		50MHz square wave (Note 2)	V _{DDA} = 5V		18	23.3	
			V _{DDA} = 3.3V		14.2	18.4	
			V _{DDA} = 2.5V		12.3	16.1	mA
Supply Compant (MANY14026)			V _{DDA} = 1.8V		10.5	13.6	
Supply Current (MAX14936_)		500kHz square wave	V _{DDB} = 5V		5.2	7.2	
			V _{DDB} = 3.3V		5.2	7.2	
			V _{DDB} = 2.5V		5.2	7.2	
			V _{DDB} = 1.8V		5	7.0	
			V _{DDB} = 5V		8.2	10.0	
		12.5MHz	V _{DDB} = 3.3V		7.2	9.1	
	I _{DDB}	square wave (Note 2)	V _{DDB} = 2.5V		6.7	8.7	
		(11010 _)	V _{DDB} = 1.8V		6.3	8.2	
			V _{DDB} = 5V		18	23.3	-
		50MHz	V _{DDB} = 3.3V		14.2	18.4	
		square wave (Note 2)	V _{DDB} = 2.5V		12.3	16.1	
			V _{DDB} = 1.8V		10.5	13.6	

DC Electrical Characteristics (continued)

 $(V_{DDA} - V_{GNDA} = +1.71 \text{V to } +5.5 \text{V}, V_{DDB} - V_{GNDB} = +1.71 \text{V to } +5.5 \text{V}, C_L = 15 \text{pF}, T_A = -40 ^{\circ}\text{C to } +125 ^{\circ}\text{C}, \text{ unless otherwise noted.}$ Typical values are at $V_{DDA} - V_{GNDA} = +3.3 \text{V}, V_{DDB} - V_{GNDB} = +3.3 \text{V}, V_{GNDA} = V_{GNDB}, T_A = +25 ^{\circ}\text{C}, \text{ unless otherwise noted.}$ (Note 1)

PARAMETER	SYMBOL	CON	NDITIONS	MIN	TYP	MAX	UNITS
LOGIC INPUTS AND OUTPUTS							
Input High Voltage	V _{IH}	ENA, INA_ relative	ENA, INA_ relative to GNDA				- V
Imput Figit Voltage	VIH	ENB, INB_ relative	ENB, INB_ relative to GNDB				
		ENA, INA_	$1.71V \le V_{DDA} \le 1.89V$			0.6	V
Input Low Voltage	V _{IL}	relative to GNDA	$2.25V \le V_{DDA} \le 5.5V$			8.0	
Impat Low Voltage	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	ENB, INB_	$1.71V \le V_{\text{DDB}} \le 1.89V$			0.6	_ *
		relative to GNDB	$2.25 \text{V} \le \text{V}_{\text{DDB}} \le 5.5 \text{V}$			8.0	
		GNDA or V _{INB} relative to	MAX1493_A/D		410		mV
Input Hysteresis	V _{HYS}		MAX1493_B/E		410		
			MAX1493_C/F		80		
Input Leakage Current	IL		V _{INA} _ = 0 or V _{DDA} , V _{INB} _ = 0 or V _{DDB}			+1	μА
Input Capacitance	C _{IN}	INA_, INB_, f = 1N	ИНz		2		pF
EN_ Pullup Current	l _{PU}			-4	-2.3	-1	μА
Output Voltage High	V	V _{OUTA} relative to GNDA, I _{OUTA} = -4mA (Note 3)		V _{DDA} - 0.4			
Output Voltage High	Voн	V _{OUTB} relative to GNDB, I _{OUTB} = -4mA (Note 3)		V _{DDB} - 0.4			V
Output Voltage Low	Va	V _{OUTA} relative to GNDA, I _{OUTA} = 4mA (Note 3)				0.4	V
Output voitage Low	V _{OL}	V _{OUTB} relative to GNDB, l _{OUTB} = 4mA (Note 3)				0.4	V

Dynamic Electrical Characteristics (MAX1493_A/D)

 $(V_{DDA} - V_{GNDA} = +1.71 \text{V to } +5.5 \text{V}, V_{DDB} - V_{GNDB} = +1.71 \text{V to } +5.5 \text{V}, C_L = 15 \text{pF}, T_A = -40 ^{\circ}\text{C to } +125 ^{\circ}\text{C}, \text{ unless otherwise noted. Typical values are at } V_{DDA} - V_{GNDA} = +3.3 \text{V}, V_{DDB} - V_{GNDB} = +3.3 \text{V}, V_{GNDA} = V_{GNDB}, T_A = +25 ^{\circ}\text{C}, \text{ unless otherwise noted.)} (Notes 1, 2)$

PARAMETER	SYMBOL		CONDITIONS	MIN	TYP	MAX	UNITS
INPUT AND OUTPUT CHANNEL	S						
Common-Mode Transient Immunity	CMTI	IN = GND_ c	or V _{DD} _(Note 4)		25		kV/μs
Maximum Data Rate	DR _{MAX}			1			Mbps
Minimum Pulse Width	PW _{MIN}	INA_ to OUTB_	, INB_ to OUTA_			1	μs
Glitch Rejection		INA_ to OUTB_	, INB_ to OUTA_		32		ns
		INA_ to	4.5V ≤ V _{DDA} , V _{DDB} ≤ 5.5V		38.2	54.1	
	4	OUTB_,	$3.0V \le V_{DDA}, V_{DDB} \le 3.6V$		38.7	54.6	
	t _{PLH}	INB_ to OUTA ,	2.25V ≤ V _{DDA} , V _{DDB} ≤ 2.75V		39.7	55.6	
Propagation Polov (Figure 1)		C _L = 15pF	1.71V ≤ V _{DDA} , V _{DDB} ≤ 1.89V		42.9	58.4	no
Propagation Delay (Figure 1)		INA_ to	4.5V ≤ V _{DDA} , V _{DDB} ≤ 5.5V		38.6	55.3	ns
	t _{PHL}	OUTB_,	$3.0V \le V_{DDA}, V_{DDB} \le 3.6V$		38.9	55.6	
		INB_ to OUTA_,	$2.25V \le V_{DDA}, V_{DDB} \le 2.75V$		39.8	56.1	
		C _L = 15pF	1.71V ≤ V _{DDA} , V _{DDB} ≤ 1.89V		42.3	60.2	1
		t _{PLH} - t _{PHL}	4.5V ≤ V _{DDA} , V _{DDB} ≤ 5.5V		0.4	4.5	- ns
Pulse-Width Distortion	PWD		$3.0V \le V_{DDA}, V_{DDB} \le 3.6V$		0.2	4.3	
	PWD		2.25V ≤ V _{DDA} , V _{DDB} ≤ 2.75V		0.1	3.9	
			1.71V ≤ V _{DDA} , V _{DDB} ≤ 1.89V		0.6	4.7	
		4.5V ≤ V _{DDA} , V	′ _{DDB} ≤ 5.5V			26.6	
	t	3.0V ≤ V _{DDA} , V	′ _{DDB} ≤ 3.6V			26.6	
	^t SPLH	$2.25V \le V_{DDA}, V_{DDB} \le 2.75V$				26.6	
Propagation Delay Skew		1.71V ≤ V _{DDA} ,	V _{DDB} ≤ 1.89V	≤1.89V 42.9 58.4 ≤5.5V 38.6 55.3 ≤3.6V 38.9 55.6 ≤2.75V 39.8 56.1 ≤1.89V 42.3 60.2 ≤5.5V 0.4 4.5 ≤3.6V 0.2 4.3 ≤2.75V 0.1 3.9 ≤1.89V 0.6 4.7	ns		
Part-to-Part (Same Channel)		4.5V ≤ V _{DDA} , V	′ _{DDB} ≤ 5.5V			27.9	115
	t	3.0V ≤ V _{DDA} , V	' _{DDB} ≤ 3.6V			27.7	
	tsphl	2.25V ≤ V _{DDA} ,	V _{DDB} ≤ 2.75V			27.6	
		1.71V ≤ V _{DDA} ,	V _{DDB} ≤ 1.89V			29.7	
		4.5V ≤ V _{DDA} , V	′ _{DDB} ≤ 5.5V			6.7	
	4	3.0V ≤ V _{DDA} , V	' _{DDB} ≤ 3.6V			6.7	
	tscslh	2.25V ≤ V _{DDA} ,	V _{DDB} ≤ 2.75V			6.7	
Propagation Delay Skew Chan-		1.71V ≤ V _{DDA} ,	V _{DDB} ≤ 1.89V			6.7	ns
nel-to-Channel (Same Direction)		4.5V ≤ V _{DDA} , V	' _{DDB} ≤ 5.5V			6.7	
	4	3.0V ≤ V _{DDA} , V	′ _{DDB} ≤ 3.6V			6.7	
	tscshl	2.25V ≤ V _{DDA} ,	V _{DDB} ≤ 2.75V			6.7	
		1.71V ≤ V _{DDA} ,	V _{DDB} ≤ 1.89V			6.7	

Dynamic Electrical Characteristics (MAX1493_A/D) (Continued)

 $(V_{DDA} - V_{GNDA} = +1.71 \text{V to } +5.5 \text{V}, V_{DDB} - V_{GNDB} = +1.71 \text{V to } +5.5 \text{V}, C_L = 15 \text{pF}, T_A = -40 ^{\circ}\text{C to } +125 ^{\circ}\text{C}, \text{ unless otherwise noted. Typical values are at } V_{DDA} - V_{GNDA} = +3.3 \text{V}, V_{DDB} - V_{GNDB} = +3.3 \text{V}, V_{GNDA} = V_{GNDB}, T_A = +25 ^{\circ}\text{C}, \text{ unless otherwise noted.)} (Notes 1, 2)$

PARAMETER	SYMBOL	C	CONDITIONS	MIN	TYP	MAX	UNITS
		4.5V ≤ V _{DDA} , V _E	_{DDB} ≤ 5.5V			26.6	
	.	$3.0V \le V_{DDA}, V_{[}$	_{DDB} ≤ 3.6V			26.6	_
	^t SCOLH	2.25V ≤ V _{DDA} , \	/ _{DDB} ≤ 2.75V			26.6	
Propagation Delay Skew		1.71V ≤ V _{DDA} , \	/ _{DDB} ≤ 1.89V			26.9	
Channel-to-Channel (Opposing Direction)		4.5V ≤ V _{DDA} , V _E	_{DDB} ≤ 5.5V			27.9	ns
,	+	$3.0V \le V_{DDA}, V_{I}$	_{DDB} ≤ 3.6V			27.7	
	t _{SCOHL}	2.25V ≤ V _{DDA} , \	/ _{DDB} ≤ 2.75V			27.6	
		1.71V ≤ V _{DDA} , \	/ _{DDB} ≤ 1.89V			29.7	
		OUTA /	4.5V ≤ V _{DDA} , V _{DDB} ≤ 5.5V		2		
Rise Time (Figure 1)	t _R	OUTB_, 10% to 90%, C _L = 15pF	3.0V ≤ V _{DDA} , V _{DDB} ≤ 3.6V		2		ns
			2.25V ≤ V _{DDA} , V _{DDB} ≤ 2.75V		2		
			1.71V ≤ V _{DDA} , V _{DDB} ≤ 1.89V		2		
	l lou	OUTA_/ OUTB_, 90% to 10%,	4.5V ≤ V _{DDA} , V _{DDB} ≤ 5.5V		2		ns
Fall Time (Figure 1)			$3.0V \le V_{DDA}, V_{DDB} \le 3.6V$		2		
raii Time (<u>Figure 1</u>)	t _F		2.25V ≤ V _{DDA} , V _{DDB} ≤ 2.75V		2		
		C _L = 15pF	1.71V ≤ V _{DDA} , V _{DDB} ≤ 1.89V		2		
			4.5V ≤ V _{DDA} , V _{DDB} ≤ 5.5V			5.1	
Enable to Data Valid	t	ENA to OUTA_, ENB to OUTB,	$3.0V \le V_{DDA}, V_{DDB} \le 3.6V$			5.5	ns
Litable to Data Valid	t _{EN}	$C_l = 15pF$	$2.25V \le V_{DDA}, V_{DDB} \le 2.75V$			6.7	115
			1.71V ≤ V _{DDA} , V _{DDB} ≤ 1.89V			16.3	
			4.5V ≤ V _{DDA} , V _{DDB} ≤ 5.5V			2.7	ns
Enable to Three-State	trou	ENA to OUTA_, ENB to OUTB,	3.0V ≤ V _{DDA} , V _{DDB} ≤ 3.6V			4.4	
Enable to Tulee-State	t _{TRI}	$C_1 = 15pF$	2.25V ≤ V _{DDA} , V _{DDB} ≤ 2.75V			7.0	
			1.71V ≤ V _{DDA} , V _{DDB} ≤ 1.89V			11.7	

Dynamic Electrical Characteristics (MAX1493_B/E)

 $(V_{DDA} - V_{GNDA} = +1.71 \text{V to } +5.5 \text{V}, V_{DDB} - V_{GNDB} = +1.71 \text{V to } +5.5 \text{V}, C_L = 15 \text{pF}, T_A = -40 ^{\circ}\text{C to } +125 ^{\circ}\text{C}, \text{ unless otherwise noted. Typical values are at } V_{DDA} - V_{GNDA} = +3.3 \text{V}, V_{DDB} - V_{GNDB} = +3.3 \text{V}, V_{GNDA} = V_{GNDB}, T_A = +25 ^{\circ}\text{C}, \text{ unless otherwise noted.)} (Notes 1, 2)$

PARAMETER	SYMBOL		CONDITIONS	MIN	TYP	MAX	UNITS
INPUT AND OUTPUT CHANNE	LS	'					
Common-Mode Transient Immunity	СМТІ	IN = GND_	or V _{DD} (Note 4)		25		kV/μs
Maximum Data Rate	DR _{MAX}			25			Mbps
Minimum Pulse Width	PW _{MIN}	INA_ to OUTE	B_, INB_ to OUTA_			40	ns
Glitch Rejection		INA_ to OUTE	B_, INB_ to OUTA_		15		ns
		INA_ to	$4.5V \le V_{DDA}, V_{DDB} \le 5.5V$		20.9	27.5	-
	tour	OUTB_,	$3.0V \le V_{DDA}, V_{DDB} \le 3.6V$		21.4	28.7	
	^t PLH	INB_ to OUTA_,	2.25V ≤ V _{DDA} , V _{DDB} ≤ 2.75V		22.4	31.2	
Proposition Polov (Figure 4)		C _L = 15pF	1.71V ≤ V _{DDA} , V _{DDB} ≤ 1.89V		25.7	36.9	
Propagation Delay (Figure 1)		INA_ to	4.5V ≤ V _{DDA} , V _{DDB} ≤ 5.5V		21.1	28.8	ns
		OUTB_,	$3.0V \le V_{DDA}, V_{DDB} \le 3.6V$		21.5	29.8	
	t _{PHL}	INB_ to OUTA_, C _L = 15pF	2.25V ≤ V _{DDA} , V _{DDB} ≤ 2.75V		22.3	31.9	
			1.71V ≤ V _{DDA} , V _{DDB} ≤ 1.89V		24.9	37.4	1
			4.5V ≤ V _{DDA} , V _{DDB} ≤ 5.5V		0.2	2.6	ns
		t _{PLH} - t _{PHL}	3.0V ≤ V _{DDA} , V _{DDB} ≤ 3.6V		0.1	2.6	
Pulse-Width Distortion	PWD		2.25V ≤ V _{DDA} , V _{DDB} ≤ 2.75V		0.1	2.4	
			1.71V ≤ V _{DDA} , V _{DDB} ≤ 1.89V		0.7	3.2	
		4.5V ≤ V _{DDA} ,	V _{DDB} ≤ 5.5V			11.7	
		3.0V ≤ V _{DDA} , V _{DDB} ≤ 3.6V				11.5	
	t _{SPLH}	2.25V ≤ V _{DDA} , V _{DDB} ≤ 2.75V				11.3	
Propagation Delay Skew			, V _{DDB} ≤ 1.89V			13.6	
Part-to-Part (Same Channel)		4.5V ≤ V _{DDA} ,				9.8	ns
		3.0V ≤ V _{DDA} ,				9.8	
	tsphl		, V _{DDB} ≤ 2.75V			11.1	
			$1.71V \le V_{DDA}, V_{DDB} \le 1.89V$			14.4	
		4.5V ≤ V _{DDA} ,				3	
		3.0V ≤ V _{DDA} ,				3	
	tscslh					3	
Propagation Delay Skew			$2.25V \le V_{DDA}, V_{DDB} \le 2.75V$ $1.71V \le V_{DDA}, V_{DDB} \le 1.89V$			3	
Channel-to-Channel		4.5V ≤ V _{DDA} ,				3	ns
(Same Direction)						3	
	tscshl		$3.0V \le V_{DDA}, V_{DDB} \le 3.6V$			3	_
			$2.25V \le V_{DDA}, V_{DDB} \le 2.75V$ $1.71V \le V_{DDA}, V_{DDB} \le 1.89V$			3	-

Dynamic Electrical Characteristics (MAX1493_B/E) (Continued)

 $(V_{DDA} - V_{GNDA} = +1.71 \text{V to } +5.5 \text{V}, V_{DDB} - V_{GNDB} = +1.71 \text{V to } +5.5 \text{V}, C_L = 15 \text{pF}, T_A = -40 ^{\circ}\text{C to } +125 ^{\circ}\text{C}, \text{ unless otherwise noted. Typical values are at } V_{DDA} - V_{GNDA} = +3.3 \text{V}, V_{DDB} - V_{GNDB} = +3.3 \text{V}, V_{GNDA} = V_{GNDB}, T_A = +25 ^{\circ}\text{C}, \text{ unless otherwise noted.)} \text{ (Notes 1, 2)}$

PARAMETER	SYMBOL	(CONDITIONS	MIN	TYP	MAX	UNITS
		$4.5V \le V_{DDA}, V_{DDA}$	_{DDB} ≤ 5.5V			11.7	
		$3.0V \le V_{DDA}, V_{DDB} \le 3.6V$				11.5	
	tSCOLH	2.25V ≤ V _{DDA} , V	/ _{DDB} ≤ 2.75V			11.3	
Propagation Delay Skew		1.71V ≤ V _{DDA} , V	/ _{DDB} ≤ 1.89V			13.6	
Channel to Channel (Opposing Direction)		4.5V ≤ V _{DDA} , V _D	_{DDB} ≤ 5.5V			9.8	ns
		3.0V ≤ V _{DDA} , V _E	_{DDB} ≤ 3.6V			9.8	
	t _{SCOHL}	2.25V ≤ V _{DDA} , V	/ _{DDB} ≤ 2.75V			11.1	
		1.71V ≤ V _{DDA} , V	/ _{DDB} ≤ 1.89V			14.4	
		OUTA /	4.5V ≤ V _{DDA} , V _{DDB} ≤ 5.5V		2		
Rise Time (Figure 1)	t _R	OUTB_, 10% to 90%, C _L = 15pF	3.0V ≤ V _{DDA} , V _{DDB} ≤ 3.6V		2		ns
			2.25V ≤ V _{DDA} , V _{DDB} ≤ 2.75V		2		
			1.71V≤V _{DDA} , V _{DDB} ≤1.89V		2		
		OUTA_/ OUTB_, 90% to 10%, C _L = 15pF	4.5V ≤ V _{DDA} , V _{DDB} ≤ 5.5V		2		ns
Fall Time (Figure 4)			$3.0V \le V_{DDA}, V_{DDB} \le 3.6V$		2		
Fall Time (Figure 1)	t _F		2.25V ≤ V _{DDA} , V _{DDB} ≤ 2.75V		2		
			1.71V≤V _{DDA} , V _{DDB} ≤1.89V		2		
			4.5V ≤ V _{DDA} , V _{DDB} ≤ 5.5V			5.1	
Enable to Data Valid		ENA to OUTA_,	3.0V ≤ V _{DDA} , V _{DDB} ≤ 3.6V			5.5	
Enable to Data Valid	t _{EN}	ENB to OUTB_, C _I = 15pF	2.25V ≤ V _{DDA} , V _{DDB} ≤ 2.75V			6.7	ns
			1.71V≤V _{DDA} , V _{DDB} ≤1.89V			16.3	
			4.5V ≤ V _{DDA} , V _{DDB} ≤ 5.5V			2.7	ns
Enable to Three-State	t	ENA to OUTA_,	$3.0V \le V_{DDA}, V_{DDB} \le 3.6V$			4.4	
Litable to Tillee-State	t _{TRI}	ENB to OUTB_, C _I = 15pF	2.25V ≤ V _{DDA} , V _{DDB} ≤ 2.75V			7.0	
			1.71V ≤ V _{DDA} , V _{DDB} ≤ 1.89V			11.7	

Dynamic Electrical Characteristics (MAX1493_C/F)

 $(V_{DDA} - V_{GNDA} = +1.71 \text{V to } +5.5 \text{V}, V_{DDB} - V_{GNDB} = +1.71 \text{V to } +5.5 \text{V}, C_L = 15 \text{pF}, T_A = -40 ^{\circ}\text{C to } +125 ^{\circ}\text{C}, \text{ unless otherwise noted. Typical values are at } V_{DDA} - V_{GNDA} = +3.3 \text{V}, V_{DDB} - V_{GNDB} = +3.3 \text{V}, V_{GNDA} = V_{GNDB}, T_A = +25 ^{\circ}\text{C}, \text{ unless otherwise noted.)} \text{ (Notes 1, 2)}$

PARAMETER	SYMBOL		CONDITIONS	MIN	TYP	MAX	UNITS
INPUT AND OUTPUT CHANNE	LS	·I		,			
Common-Mode Transient Immunity	CMTI	IN = GND_	or V _{DD} (Note 4)		25		kV/µs
Maximum Data Rate	DR _{MAX}			150	,		Mbps
Minimum Pulse Width	PW _{MIN}	INA_ to OUTE	INA_ to OUTB_, INB_ to OUTB_			6.67	ns
		INA_ to	4.5V ≤ V _{DDA} , V _{DDB} ≤ 5.5V		5.1	7.5	
		OUTB_,	3.0V ≤ V _{DDA} , V _{DDB} ≤ 3.6V		5.2	8.1	
	t _{PLH}	INB_ to OUTA_,	2.25V ≤ V _{DDA} , V _{DDB} ≤ 2.75V		5.8	9.7	
Propagation Delay (Figure 1)		C _L = 15pF	1.71V ≤ V _{DDA} , V _{DDB} ≤ 1.89V		8.1	14	ne
Propagation Delay (<u>Figure 1</u>)		INA_ to	4.5V ≤ V _{DDA} , V _{DDB} ≤ 5.5V		4.9	7.4	ns
	t _{PHL}	OUTB_, INB_ to OUTA_, C _L = 15pF	$3.0V \le V_{DDA}, V_{DDB} \le 3.6V$		5.3	8.3	
			$2.25V \le V_{DDA}, V_{DDB} \le 2.75V$		5.9	10.2	
			1.71V ≤ V _{DDA} , V _{DDB} ≤ 1.89V		8.2	14.9	
		t _{PLH} - t _{PHL}	$4.5V \le V_{DDA}, V_{DDB} \le 5.5V$		0.2	1	
Dulas Width Distantian	DWD		3.0V ≤ V _{DDA} , V _{DDB} ≤ 3.6V		0.1	1	ns
Pulse-Width Distortion	PWD		2.25V ≤ V _{DDA} , V _{DDB} ≤ 2.75V		0.1	1	
			1.71V ≤ V _{DDA} , V _{DDB} ≤ 1.89V		0.1	1	
		$4.5V \le V_{DDA}, V_{DDB} \le 5.5V$				3.0	
		$3.0V \le V_{DDA}, V_{DDB} \le 3.6V$				3.3	
	tsplh	2.25V ≤ V _{DDA} , V _{DDB} ≤ 2.75V				4.3	
Propagation Delay Skew Part-		1.71V ≤ V _{DDA} , V _{DDB} ≤ 1.89V				7.1	no
to-Part (Same Channel)		4.5V ≤ V _{DDA} ,	V _{DDB} ≤ 5.5V			2.8	ns
		3.0V ≤ V _{DDA} ,	V _{DDB} ≤ 3.6V			3.4	
	tsphl	2.25V ≤ V _{DDA}	, V _{DDB} ≤ 2.75V			4.6	
		1.71V ≤ V _{DDA} , V _{DDB} ≤ 1.89V				7.9	1
		4.5V ≤ V _{DDA} ,	V _{DDB} ≤ 5.5V			0.9	
		3.0V ≤ V _{DDA} ,	V _{DDB} ≤ 3.6V			1.2	
	tscslh	2.25V ≤ V _{DDA}	, V _{DDB} ≤ 2.75V			1.4	
Propagation Delay Skew		1.71V ≤ V _{DDA} , V _{DDB} ≤ 1.89V				1.6	F-2
Channel-to-Channel (Same Direction)		4.5V ≤ V _{DDA} ,	V _{DDB} ≤ 5.5V			0.9	ns
		3.0V ≤ V _{DDA} ,	V _{DDB} ≤ 3.6V			1.2	
	tscshl	2.25V ≤ V _{DDA}			1.4		
		1.71V ≤ V _{DDA}	A, V _{DDB} ≤ 1.89V			1.6	1

Dynamic Electrical Characteristics (MAX1493_C/F) (continued)

 $(V_{DDA} - V_{GNDA} = +1.71 \text{V to } +5.5 \text{V}, V_{DDB} - V_{GNDB} = +1.71 \text{V to } +5.5 \text{V}, C_L = 15 \text{pF}, T_A = -40 ^{\circ}\text{C to } +125 ^{\circ}\text{C}, \text{ unless otherwise noted. Typical values are at } V_{DDA} - V_{GNDA} = +3.3 \text{V}, V_{DDB} - V_{GNDB} = +3.3 \text{V}, V_{GNDA} = V_{GNDB}, T_A = +25 ^{\circ}\text{C}, \text{ unless otherwise noted.)} \text{ (Notes 1, 2)}$

PARAMETER	SYMBOL	(CONDITIONS	MIN	TYP	MAX	UNITS
		4.5V ≤ V _{DDA} , V _D	_{DDB} ≤ 5.5V			3	
	_	$3.0V \le V_{DDA}, V_{DDB} \le 3.6V$				3.3	
	tscolh	2.25V ≤ V _{DDA} , V	_{DDB} ≤ 2.75V			4.3	
Propagation Delay Skew		1.71V ≤ V _{DDA} , V	' _{DDB} ≤ 1.89V			7.1	ns
Channel-to-Channel (Opposing Direction)		4.5V ≤ V _{DDA} , V _D	_{DDB} ≤ 5.5V			2.8	
,	t	$3.0V \le V_{DDA}, V_{DDA}$	_{DDB} ≤ 3.6V			3.4	
	tscohl t	2.25V ≤ V _{DDA} , V	' _{DDB} ≤ 2.75V			4.6	
		1.71V ≤ V _{DDA} , V	' _{DDB} ≤ 1.89V			7.9	
		OUTA /	4.5V ≤ V _{DDA} , V _{DDB} ≤ 5.5V		2		
Pico Timo (Figuro 1)	+_	OUTB_,	$3.0V \le V_{DDA}, V_{DDB} \le 3.6V$		2		no
Rise Time (<u>Figure 1</u>)	^t R	10% to 90%, C _L = 15pF	$2.25V \le V_{DDA}, V_{DDB} \le 2.75V$		2		ns -
			1.71V ≤ V _{DDA} , V _{DDB} ≤ 1.89V		2		
		OUTA_/ OUTB_, 90% to 10%, C _L = 15pF	$4.5V \le V_{DDA}, V_{DDB} \le 5.5V$		2		- ns
Fall Time (Figure 4)	t _F		$3.0V \le V_{DDA}, V_{DDB} \le 3.6V$		2		
Fall Time (<u>Figure 1</u>)			$2.25V \le V_{DDA}, V_{DDB} \le 2.75V$		2		
			1.71V ≤ V _{DDA} , V _{DDB} ≤ 1.89V		2		
			4.5V ≤ V _{DDA} , V _{DDB} ≤ 5.5V			5.1	ns
Enable to Data Valid	t	ENA to OUTA_, ENB to OUTB ,	$3.0V \le V_{DDA}, V_{DDB} \le 3.6V$			5.5	
Lilable to Data Valid	t _{EN}	$C_1 = 15pF$	$2.25V \le V_{DDA}, V_{DDB} \le 2.75V$			6.7	
			1.71V ≤ V _{DDA} , V _{DDB} ≤ 1.89V			16.3	
			$4.5V \le V_{DDA}, V_{DDB} \le 5.5V$			2.7	
Enable to Three-State	t	ENA to OUTA_, ENB to OUTB_,	$3.0V \le V_{DDA}, V_{DDB} \le 3.6V$			4.4	ns
Enable to Three-State	t _{TRI}	$C_1 = 15pF$	$2.25V \le V_{DDA}, V_{DDB} \le 2.75V$			7.0	115
			V _{DDA} , V _{DDB} ≤ 1.89V			11.7	
		V _{DDA} , V _{DDB} = 5	.0V		140		
Peak Eye Diagram Jitter	T=.	$V_{DDA}, V_{DDB} = 3$.3V		130		- ps
T ear Lye Diagram Julei	T _{JIT(PK)}	$V_{DDA}, V_{DDB} = 2$.5V		140		
		$V_{DDA}, V_{DDB} = 1$.8V		160		

ESD Protection

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
ESD		Human Body Model, All Pins		±4		kV

- Note 1: All devices are 100% production tested at TA = +125°C. Specifications over temperature are guaranteed by design.
- Note 2: Not production tested. Guaranteed by design.
- Note 3: All currents into the device are positive. All currents out of the device are negative.
- Note 4: CMTI is the maximum sustainable common-mode voltage slew rate while maintaining the correct output. CMTI applies to both rising and falling common-mode voltage edges. Tested with the transient generator connected between GNDA and GNDB (V_{CM} = 1000V).

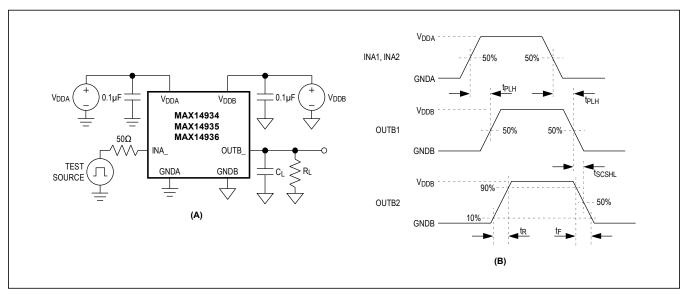


Figure 1. Test Circuit (A) and Timing Diagram (B)

Safety Regulatory Approvals

UL

The MAX14934-MAX14936 are certified under UL1577. For more details, refer to File E351759

Rated up to 5000V_{RMS} isolation voltage for single protection.

cUL (Equivalent to CSA notice 5A)

The MAX14934-MAX14936 are certified up to 5000V_{RMS} for single protection. For more details, refer to File E351759.

VDE

The MAX14934-MAX14936 are certified to DIN VDE V 0884-11: 2017-01. For details, see file ref. 5015017-4880-0001/272147/TL7/ SCT. Basic Insulation, Maximum Transient Isolation Voltage 8400V_{PK}, Maximum Repetitive Peak Isolation Voltage 1200V_{PK}

This coupler is suitable for "safe electrical insulation" only within the safety ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.

IEC Insulation Testing

TUV

The MAX14934-MAX14936 are tested under TUV.

IEC 60950-1: Up to 1200V_{PK} (848V_{RMS}) working voltage for basic insulation.

IEC 61010-1 (ed. 3): Up to 848V_{RMS} working voltage for basic insulation. For details, see Technical Report number 095-72100581-100.

IEC 60601-1 (ed. 3): For details see Technical Report number 095-72100581-200.

Basic insulation 1 MOOP, 1200V_{PK} (848V_{RMS})

Withstand isolation voltage (V_{ISO}) for 60s, 5000V_{RMS}

MAX14934-MAX14936 Insulation Characteristics

PARAMETER	SYMBOL	CONDITIONS	VALUE	UNITS
Partial Discharge Test Voltage	V _{PR}	Method B1 = V _{IORM} x 1.875 (t = 1s, partial discharge < 5pC)	2250	V _P
Maximum Repetitive Peak Isolation Voltage	V _{IORM}	(Note 5)	1200	V _P
Maximum Working Isolation Voltage	V _{IOWM}	Continuous RMS voltage (Note 5)	848	V _{RMS}
Maximum Transient Isolation Voltage	V _{IOTM}	t = 1s (Note 5)	8400	V _P
Maximum Withstand Isolation Voltage	V _{ISO}	f _{SW} = 60Hz, duration = 60s (Note 5, 6)	5000	V _{RMS}
Maximum Surge Isolation Voltage	V _{IOSM}	Basic insulation, 1.2/50µs pulse per IEC 61000-4-5 (Note 5, 7)	10	kV
		V _{IO} = 500V, T _A = 25°C	> 10 ¹²	
Insulation Resistance	R _{IO}	V _{IO} = 500V, 100°C ≤ T _A ≤ 125°C	> 10 ¹¹	Ω
		V _{IO} = 500V at T _S = 150°C	> 10 ⁹	
Barrier Capacitance Side A to Side B	C _{IO}	f _{SW} = 1MHz (Note 8)	2	pF
Minimum Creepage Distance	CPG	Wide SOIC	8	mm
Minimum Clearance Distance	CLR	Wide SOIC	8	mm
Internal Clearance		Distance through insulation	0.015	mm
Comparative Tracking Index	CTI	Material Group II (IEC 60112)	575	
Climatic Category			40/125/21	
Pollution Degree (DIN VDE 0110, Table 1)			2	

Note 5: V_{ISO} , V_{IOTM} , V_{IOSM} , V_{IOWM} , and V_{IORM} are defined by the IEC 60747-5-5 standard. Note 6: Products are qualified at V_{ISO} for 60s and 100% production tested at 120% of V_{ISO} for 1s.

Note 7: Devices are immersed in oil during surge characterization.

Note 8: Capacitance is measured with all pins on field-side and logic-side tied together.

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Safety Limits

Damage to the IC can result in a low-resistance path to ground or to the supply and, without current limiting, the MAX14934–MAX14936 could dissipate excessive amounts of power. Excessive power dissipation can damage the die and result in damage to the isolation barrier, potentially causing downstream issues. Table 1 shows the safety limits for the MAX14934–MAX14936.

The maximum safety temperature (T_S) for the device is the 150°C maximum junction temperature specified in the <u>Absolute Maximum Ratings</u>. The power dissipation (P_D) and junction-to-ambient thermal impedance (θ_{JA})

determine the junction temperature. Thermal impedance values (θ_{JA} and θ_{JC}) are available in the <u>Package Information</u> section of the datasheet. Calculate the junction temperature (T_{J}) as:

$$T_J = T_A + (P_D \times \theta_{JA})$$

<u>Figure 2</u> to <u>Figure 3</u> show the thermal derating curves for the safety power limiting and safety current limiting of the devices. Ensure that the junction temperature does not exceed 150°C.

Table 1. Safety Limiting Values for the MAX14934–MAX14936

PARAMETER	SYMBOL	TEST CONDITIONS		UNITS
Safety Current on Any Pin (No Damage to Isolation Barrier)	IS	T _J = 150°C, T _A = 25°C	300	mA
Total Safety Power Dissipation	PS	T _J = 150°C, T _A = 25°C	1760	mW
Maximum Safety Temperature	T _S		150	°C

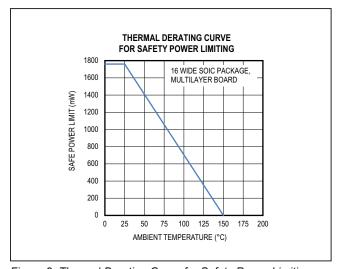


Figure 2. Thermal Derating Curve for Safety Power Limiting

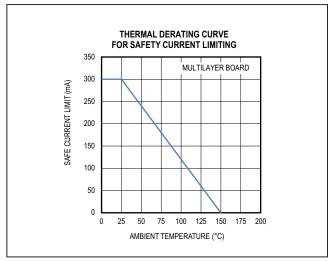
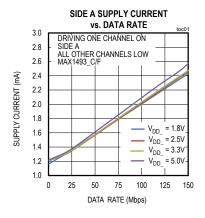
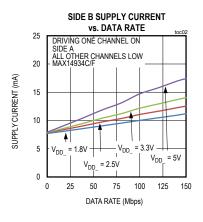


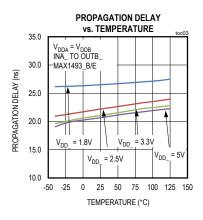
Figure 3. Thermal Derating Curve for Safety Current Limiting

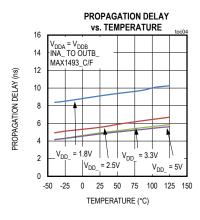
Typical Operating Characteristics

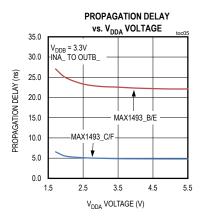
 $(V_{DDA} - V_{GNDA} = +3.3V, V_{DDB} - V_{GNDB} = +3.3V, V_{GNDA} = V_{GNDB}, T_{A} = +25$ °C, unless otherwise noted.)

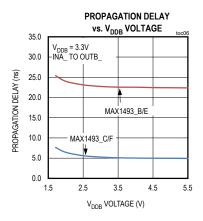


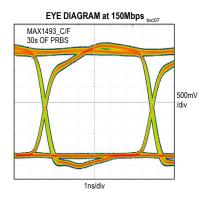


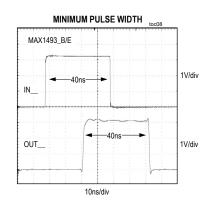


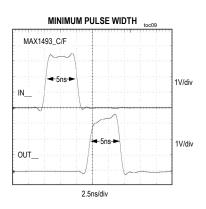




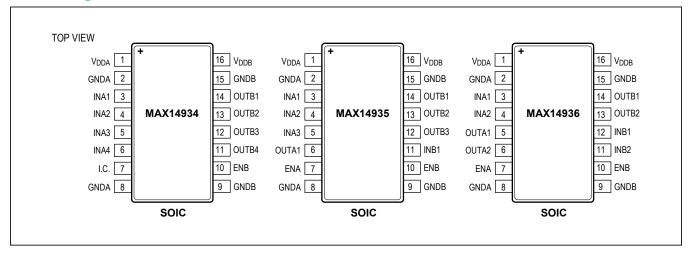








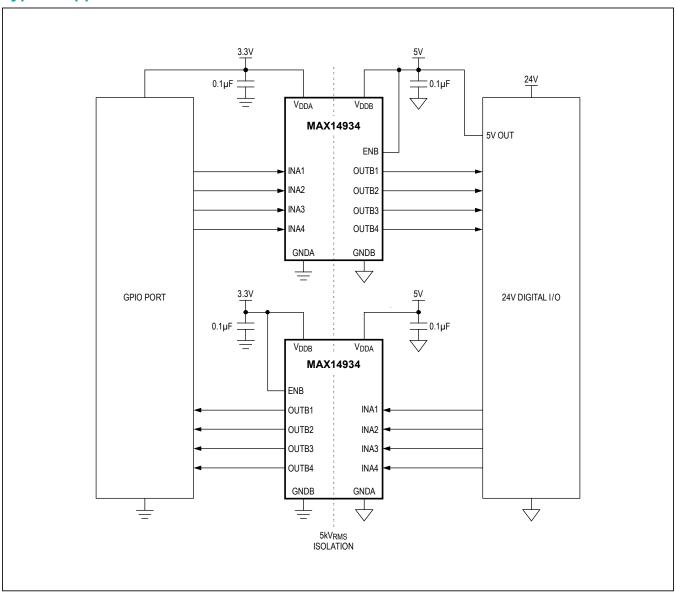
Pin Configurations



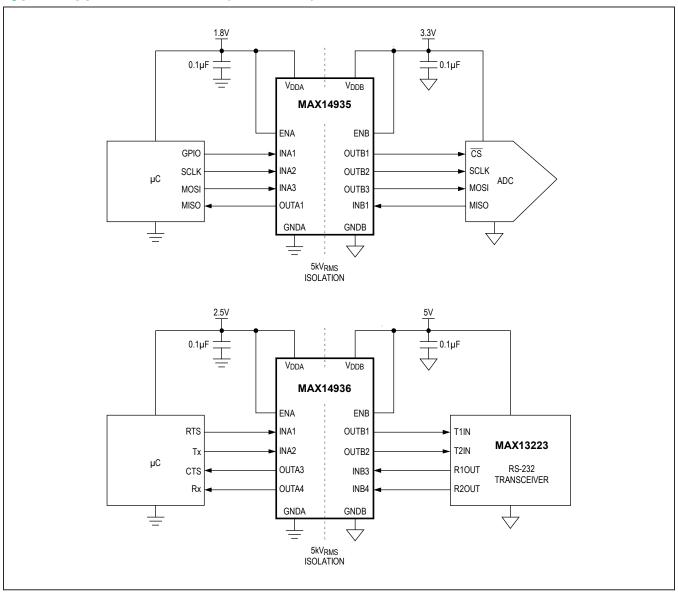
Pin Description

PIN		NAME	FUNCTION	VOLTAGE	
MAX14934	MAX14935	MAX14936	INAIVIE	FUNCTION	RELATIVE TO
1	1	1	V_{DDA}	Power Supply. Bypass V _{DDA} with a 0.1µF ceramic capacitor as close as possible to the pin.	GNDA
2, 8	2, 8	2, 8	GNDA	Ground Reference for Side A	_
3	3	3	INA1	Logic Input 1 on Side A. INA1 corresponds to OUTB1.	GNDA
4	4	4	INA2	Logic Input 2 on Side A. INA2 corresponds to OUTB2.	GNDA
5	5	_	INA3	Logic Input 3 on Side A. INA3 corresponds to OUTB3.	GNDA
6	_	_	INA4	Logic Input 4 on Side A. INA4 corresponds to OUTB4.	GNDA
7	_	_	I.C.	Internally Connected. Leave unconnected or connect to GNDA or V _{DDA} .	_
_	6	5	OUTA1	Logic Output 1 on Side A	GNDA
_	_	6	OUTA2	Logic Output 2 on Side A	GNDA
_	7	7	ENA	Active-High Enable for Side A. ENA has an internal 2μA pullup to V _{DDA} .	GNDA
9, 15	9, 15	9, 15	GNDB	Ground Reference for Side B	_
10	10	10	ENB	Active-High Enable for Side B. ENB has an internal $2\mu A$ pullup to V_{DDB} .	GNDB
11	_	_	OUTB4	Logic Output 4 on Side B	GNDB
_	11	12	INB1	Logic Input 1 on Side B. INB1 corresponds to OUTA1.	GNDB
_	_	11	INB2	Logic Input 2 on Side B. INB2 corresponds to OUTA2.	GNDB
12	12	_	OUTB3	Logic Output 3 on Side B	GNDB
13	13	13	OUTB2	Logic Output 2 on Side B	GNDB
14	14	14	OUTB1	Logic Output 1 on Side B	GNDB
16	16	16	V_{DDB}	Power Supply. Bypass V _{DDB} with a 0.1µF ceramic capacitor as close as possible to the pin.	GNDB

Typical Application Circuits



Typical Application Circuits (continued)



Detailed Description

The MAX14934–MAX14936 are a family of four-channel digital isolators. The MAX14934–MAX14936 family transfers digital signals between circuits with different power domains. The devices are rated for 5kV_{RMS} isolation voltage for 60 seconds. This family of digital isolators offers low-power operation, high electromagnetic interference (EMI) immunity, and stable temperature performance through Maxim's proprietary process technology. The devices isolate different ground domains and block high-voltage/high-current transients from sensitive or human interface circuitry.

The MAX14934–MAX14936 family offers three unidirectional channel configurations for design convenience. The MAX14934 features four channels transferring digital signals in one direction for applications such as isolated digital I/O. The MAX14935 has three channels transmitting data in one direction and one channel transmitting in the opposite direction, making it ideal for applications such as isolated SPI and RS-485 communication. The MAX14936 provides further design flexibility with two channels in each direction for isolated RS-232 or other applications.

Devices are available with data rates from DC up to 1Mbps (A/D versions), 25Mbps (B/E versions), or 150Mbps (C/F versions). Each device can also be ordered with default-high or default-low outputs. This is the state an output will go to when the input side of the device is unpowered.

The devices have two supply inputs, V_{DDA} and V_{DDB} , that independently set the logic levels on either side of the device. V_{DDA} and V_{DDB} are referenced to GNDA and GNDB, respectively. The MAX14934–MAX14936 family also features a refresh circuit to ensure output accuracy when an input remains in the same state indefinitely.

Digital Isolation

The MAX14934–MAX14936 family provides galvanic isolation for digital signals that are transmitted between two ground domains. Up to 1200V_{PEAK} of continuous isolation is supported, as well as transient differences of up to 5kV_{RMS} for up to 60 seconds.

Level Shifting

The wide supply voltage range of both V_{DDA} and V_{DDB} allows the MAX14934–MAX14936 family to be used for level translation in addition to isolation. V_{DDA} and V_{DDB} can be independently set to any voltage from 1.71V to 5.5V. The supply voltage sets the logic level on the corresponding side of the isolator.

Unidirectional Channels

Each channel of the MAX14934–MAX14936 is unidirectional; it only passes data in one direction, as indicated in the functional diagram. Each device features four unidirectional channels that operate independently with guaranteed data rates from DC up to 1Mbps (A/D versions), 25Mbps (B/E versions), or 150Mbps (C/F versions). The output driver of each channel is push-pull, eliminating the need for pullup resistors. The outputs are able to drive both TTL and CMOS logic inputs.

Startup and Undervoltage Lockout

The V_{DDA} and V_{DDB} supplies are both internally monitored for undervoltage conditions. Undervoltage events can occur during power-up, power-down, or during normal operation due to a sagging supply voltage. When an undervoltage condition is detected on either supply, all outputs go to their default states regardless of the status of the inputs (<u>Table 2</u>). <u>Figure 4</u> through <u>Figure 7</u> show the behavior of the outputs during power-up and power-down.

Applications Information

Power-Supply Sequencing

The MAX14934–MAX14936 do not require special power-supply sequencing. The logic levels are set independently on either side by V_{DDA} and V_{DDB} . Each supply can be present over the entire specified range regardless of the level or presence of the other supply.

Power-Supply Decoupling

To reduce ripple and the chance of introducing data errors, bypass V_{DDA} and V_{DDB} with 0.1 μ F ceramic capacitors to GNDA and GNDB, respectively. Place the bypass capacitors as close to the power-supply input pins as possible.

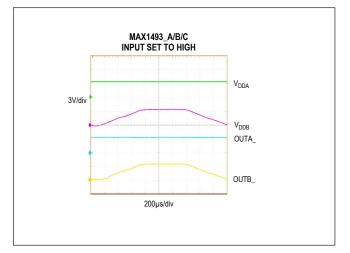
Layout Considerations

The PCB designer should follow some critical recommendations in order to get the best performance from the design.

- Keep the input/output traces as short as possible. To keep signal paths low-inductance, avoid using vias.
- Have a solid ground plane underneath the high-speed signal layer.
- Keep the area underneath the MAX14934–MAX14936 free from ground and signal planes. Any galvanic or metallic connection between the Side A and Side B defeats the isolation.

ENA ENB V_{IN} V_{DDB} V_{DDA} VOUTA **V_{OUTB}** 1 1 1 Powered Powered 0 0 Hi-Z Hi-Z 1 1 0 Powered Powered 0 0 Hi-Z Hi-Z Default Default 1 1 Χ Undervoltage Powered Hi-Z Hi-Z 0 0 1 1 Default Default Χ Powered Undervoltage 0 0 Hi-Z Hi-Z

Table 2. Output Behavior During Undervoltage Conditions



MAX1493_A/B/C
INPUT SET TO LOW

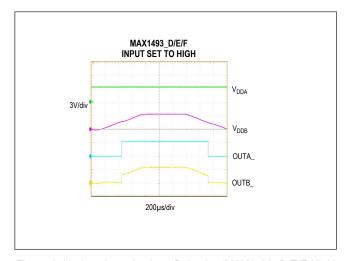
VDDA

VDDB
OUTA_

200µs/div

Figure 4. Undervoltage Lockout Behavior (MAX1493_A/B/C High)

Figure 5. Undervoltage Lockout Behavior (MAX1493_A/B/C Low)





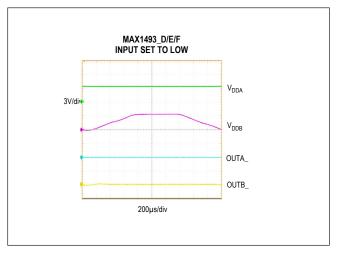
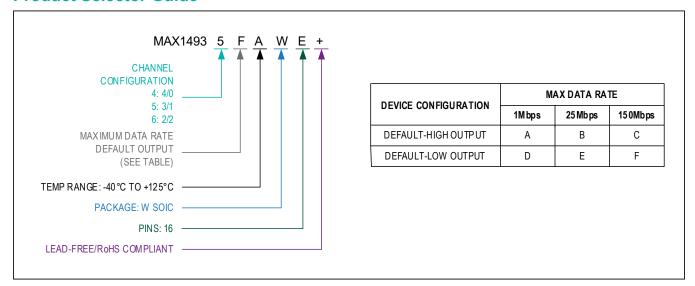


Figure 7. Undervoltage Lockout Behavior (MAX1493_D/E/F Low)

Product Selector Guide



Ordering Information

PART	CHANNEL CONFIGURATION	DATA RATE (Mbps)	OUTPUT	TEMP RANGE (°C)	PIN-PACKAGE
MAX14934AAWE+	4/0	1	Default high	-40 to +125	16 wide SOIC
MAX14934BAWE+	4/0	25	Default high	-40 to +125	16 wide SOIC
MAX14934CAWE+	4/0	150	Default high	-40 to +125	16 wide SOIC
MAX14934DAWE+	4/0	1	Default low	-40 to +125	16 wide SOIC
MAX14934EAWE+	4/0	25	Default low	-40 to +125	16 wide SOIC
MAX14934FAWE+	4/0	150	Default low	-40 to +125	16 wide SOIC
MAX14935AAWE+	3/1	1	Default high	-40 to +125	16 wide SOIC
MAX14935BAWE+	3/1	25	Default high	-40 to +125	16 wide SOIC
MAX14935CAWE+	3/1	150	Default high	-40 to +125	16 wide SOIC
MAX14935DAWE+	3/1	1	Default low	-40 to +125	16 wide SOIC
MAX14935EAWE+	3/1	25	Default low	-40 to +125	16 wide SOIC
MAX14935FAWE+	3/1	150	Default low	-40 to +125	16 wide SOIC
MAX14936AAWE+	2/2	1	Default high	-40 to +125	16 wide SOIC
MAX14936BAWE+	2/2	25	Default high	-40 to +125	16 wide SOIC
MAX14936CAWE+	2/2	150	Default high	-40 to +125	16 wide SOIC
MAX14936DAWE+	2/2	1	Default low	-40 to +125	16 wide SOIC
MAX14936EAWE+	2/2	25	Default low	-40 to +125	16 wide SOIC
MAX14936FAWE+	2/2	150	Default low	-40 to +125	16 wide SOIC

⁺Denotes a lead(Pb)-free/RoHS-compliant package.

Chip Information

PROCESS: BiCMOS

Revision History

REVISION NUMBER	REVISION DATE	DESCRIPTION	PAGES CHANGED
0	9/14	Initial release	_
1	12/14	Removed future product notation from MAX14935DAWE+ in <i>Ordering Information</i> table, changed "basic insulation" to "single protection" in <i>Safety Regulatory Approvals</i> table, and updated third bullet of <i>Many Options Support Broad Applications</i> in <i>Features and Benefits</i> section.	1, 13, 22
2	3/15	Changed future product status for: MAX14934DAWE+, MAX14936AAWE+, MAX14936BAWE+, MAX14936DAWE+, MAX14936EAWE+, and MAX14936FAWE+.	22
3	7/15	Updated Benefits and Features section, Safety Regulatory Approvals, Insulation Characteristics tables, and Pin Configuration tables.	1, 13, 14, 16
4	4/16	Fixed typos, updated Safety Regulatory Approvals, and updated Ordering Information/ Selection Guide.	1, 13, 14, 21
5	5/16	Updated TUV information and created IEC Insulation Testing table	1, 13
6	1/17	Updated Figure 1 text and removed VDE pending	1, 13, 14
9	11/20	Updated General Description, Dynamic Electrical Characteristics (MAX1493_A/D), Dynamic Electrical Characteristics (MAX1493_B/E), Dynamic Electrical Characteristics (MAX1493_C/F), Safety Regulatory Approvals, Typical Operating Circuits, and Layout Considerations sections; added Safety Limits and Product Selector Guide sections; added new Figures 2 and 3, and renumbered subsequent figures; added Table 1 and renumbered subsequent tables; added a Product Selector Guide	1, 5–10, 14–24

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<u>MAX14935EAWE+</u> <u>MAX14935BAWE+</u> <u>MAX14935CAWE+</u> <u>MAX14935EAWE+T</u> <u>MAX14935FAWE+T</u> MAX14935DAWE+T

Other:

MAX14935DAWE+ MAX14935FAWE+ MAX14935BAWE+T MAX14935CAWE+T